



Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	160	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	96	
I_{DM}	Pulsed Drain Current	640	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	125	W
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V

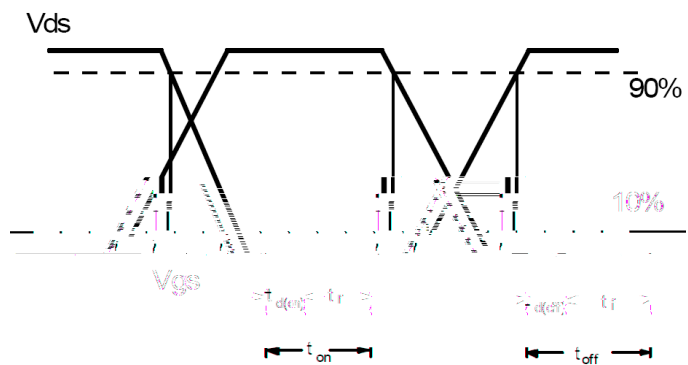
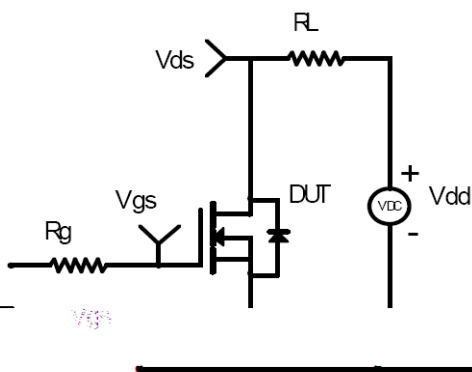
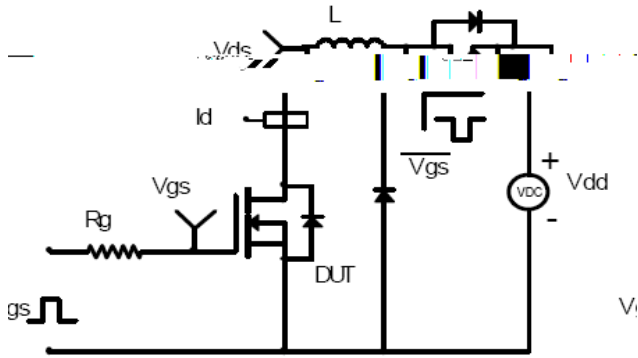
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Symbol	Characterizes	Typ.	Max.	Units
	Junction-to-case			°C
	Junction-to-ambient ($t \leq 10s$)			°C

°C

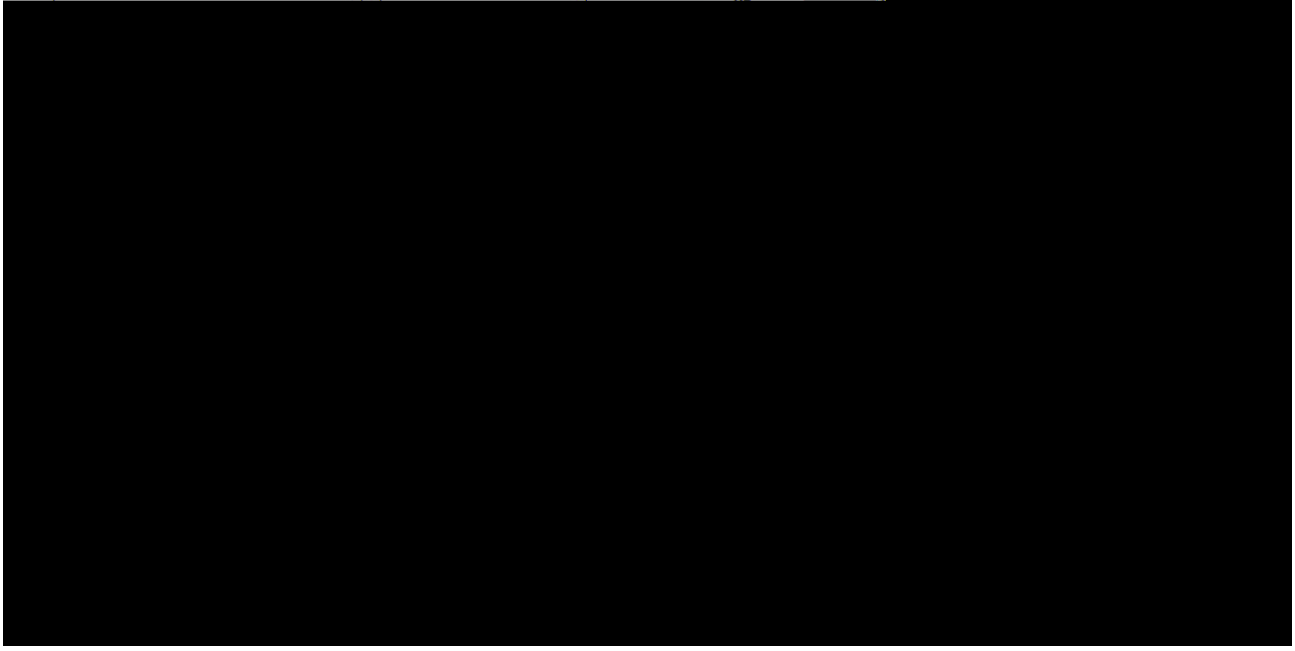
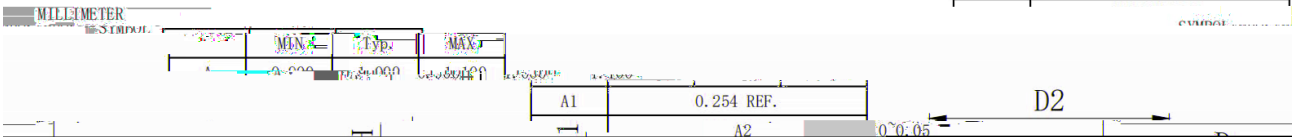
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	60			V	$V_{GS} = 0V, I_D$
$R_{DS(on)}$	Static Drain-to-Source on-resistance		1.9	2.5	m	$V_{GS}=10V, I_D = 20A$
			2.5	3.3		$V_{GS}=4.5V, I_D = 15A$



Calculated continuous current based on maximum allowable junction temperature.

- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

The value of θ_{jc} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$





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